Total No. of printed pages = 3 ECE 181407 28/7/12 Roll No. of candidate AL LIBRARY 2022Azera, Harkhowacara. Guwansa 781017 B.Tech. 4th Semester End-Term Examination APPLIED ELECTRONICS (New Regulation & New Syllabus) Full Marks - 70 Time - Three hours The figures in the margin indicate full marks for the questions. Answer Question No. 1 and any four from the rest. Answer the following: 1. $(10 \times 1 = 10)$ An intrinsic semiconductor at the absolute zero temperature (b) has large number of holes behaves like an insulator has large number of electrons (d) behaves like conductor (c) (ii) Electron-hole pairs are produced by (a) doping (b) thermal energy ionization (c) (d) Both (a) and (b) (iii) The cut in voltage of a Silicon diode is $0.2 \, \mathrm{V}$ (a) 0.6 V (b) (c) 0.8 V (d) 1.0 V (iv) A transistor has an α of 0.975. The value of β is 43 (a) (b) 39 0.995 (c) (d) 80

(v) A photodiode is a two terminal PN junction operates in

- (a) reverse bias
- (b) forward bias
- (c) both forward and reverse bias
- (d) None of the above

		(a)	register		(b)	memory		
		(c)	flip-flop		(d)	NOR gate		
	(vii)	An	XOR function is expre	ssed as				
		(a)	$\overline{AB} + AB$		(b)	$\overline{A}B + A\overline{B}$		
		(c)	$(\overline{A} + B)(A + \overline{B})$		(d)	$(\overline{A} + \overline{B})(A + B)$		
	(viii	(viii) The robot designed with polar coordinate system has						
		(a)	three linear moveme	nts				
		(b)	three rotational mov	ements				
		(c)	two linear and one r	otational	move	ement		
		(d)	two rotational and o	ne linear	move	ement		
	(ix)	Tac	hogenerator is used to	measure		- 15 P		
		(a)	force	4		SHI CHOWLE H		
		(b)	displacement			And the second second		
		(c)	angular velocity of a	rotating	shaft		-	
		(d)	temperature					
	(x)		number of moveable robot determines	joints in t	he b	ase, the arm and the end effect	ors o	
		(a)	flexibility		(b)	payload capacity		
		(c)	degree of freedom		(d)	None of the above		
2.	(a)	Differentiate between N-type and P-type semiconductors materials. Name three acceptor and three donor materials for doping of a semiconductor. $(3+2=5)$						
	(b)	Exp	lain the generation of	holes an	d ele	ctrons in an intrinsic semicondu	ctor (5)	
	(c)	Disc	cuss the process of form	mation of	depl	etion layer at PN junction.	(5)	
3.	(a)	Explain the two-breakdown mechanism of a reverse biased diode. (6						
	(b)	Draw the circuit symbol and also draw the V-I characteristics of a PN junction diode when it is (i) forward biased and (ii) reverse biased. $(1+5=6)$						
		3					.0)	

(vi) A digital circuit that can store only one bit is called

	(0)	break-down state i.e $V_z = 10$ v. Assume R (series resistance) = $R_L = 1 \text{ K}\Omega$) and maximum allowable Zener current $l_{zmax} = 20 \text{ mA}$.				
4.	(a)	Illustrate with necessary figures, explain the principle of operation of transistor.	of a PNP (6)			
	(b)	What is Q point? Draw the circuit diagram of an inverting amplifulderive the expression of output voltage. (1	ier. Also + 4 = 5)			
	(c)	Explain the following terms of an op-amp: (2	+2 = 4)			
		(i) CMRR (ii) Input offset voltage				
5.	(a)	Subtract 14 from 45 using 8 bit 2's complement arithmetic.	(4)			
	(b)	Convert the following:	× 1 = 4)			
		(i) (52) ₁₀ to binary BINA CHOVENING COMPALLIBRARY				
		(ii) (11011) ₂ to decimal				
		(iii) (110101) ₂ to octal				
		(iv) (1011011011) ₂ to hexadecimal				
	(c)	Convert the expression $f(A, B, C) = A + ABC$ in standard sop form. the expression $\sum m$ (0, 2, 3, 4, 5, 6) using K map and implement AOI logic. (2				
6.	(a)	Draw a full adder circuit and explain its operation.	(7)			
	(b)	Design a 4:16 decoder from two 3:8 decoder.	(3)			
	(c)	Design a 2bit asynchronous up counter using JR flipflop.	(5)			
7.	(a)	What is sensor? List the four factors the need to be considered in selecting a sensor. (5)				
	(b)	Explain the working principle of techogenerator.	(5)			
	(c)	Illustrate with figures, the three common robotic configurations.	(5)			